NTZD3155C

[MOSFET](#) – Small Signal, Complementary with ESD Protection, SOT-563

20 V, 540 mA / -430 mA

Features

- Leading Trench Technology for Low $R_{DS(on)}$ Performance
- High Efficiency System Performance
- Low Threshold Voltage
- ESD Protected Gate
- Small Footprint 1.6 x 1.6 mm
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC−DC Conversion Circuits
- Load/Power Switching with Level Shift
- Single or Dual Cell Li−Ion Battery Operated Systems
- High Speed Circuits
- Cell Phones, MP3s, Digital Cameras, and PDAs

ON Semiconductor®

$V_{(BR)DSS}$	$R_{DS(on)}$ **Typ**	I_D **Max** (Note 1)
N−Channel 20 V	0.4 Ω @ 4.5 V	540 mA
	0.5 Ω @ 2.5 V	
	0.7 Ω @ 1.8 V	
P−Channel −20 V	0.5 Ω @ −4.5 V	−430 mA
	0.6 Ω @ −2.5 V	
	1.0 Ω @ −1.8 V	

PINOUT: SOT−563

Top View
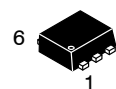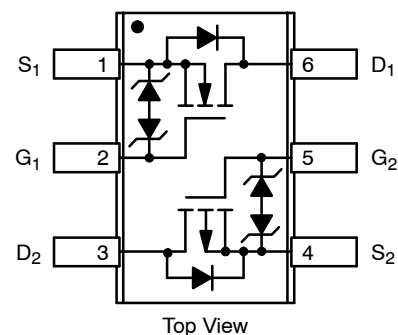
SOT−563−6
CASE 463A

MARKING DIAGRAM

TW	= Specific Device Code
M	= Date Code
▪	= Pb−Free Package

(Note: Microdot may be in either location)

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	20	V
Gate−to−Source Voltage			V_{GS}	±6	V
N−Channel Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	540	mA
		T_A = 85°C		390	
	t ≤ 5 s	T_A = 25°C		570	
P−Channel Continuous Drain Current (Note 1)	Steady State	T_A = 25°C		−430	
		T_A = 85°C		−310	
	t ≤ 5 s	T_A = 25°C		−455	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	250	mW
	t ≤ 5 s			280	
Pulsed Drain Current	N−Channel	t_p = 10 μs	I_{DM}	1500	mA
	P−Channel			−750	
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface−mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq [1 oz] including traces).

ORDERING INFORMATION

Device	Package	Shipping[†]
NTZD3155CT1G	SOT−563 (Pb−Free)	4000 / Tape & Reel
NTZD3155CT2G		4000 / Tape & Reel
NTZD3155CT5G		8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTZD3155C

Thermal Resistance Ratings

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	500	°C/W
Junction−to−Ambient − t = 5 s (Note 2)		447	

2. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	N/P	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS								
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	N	V_{GS} = 0 V	I_D = 250 μA	20			V
		P		I_D = −250 μA	−20			
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$					18		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	N	V_{GS} = 0 V, V_{DS} = 16 V	T_J = 25°C			1.0	μA
		P	V_{GS} = 0 V, V_{DS}= −16 V				−1.0	
		N	V_{GS} = 0 V, V_{DS} = 16 V	T_J = 125°C			2.0	μA
		P	V_{GS} = 0 V, V_{DS}= − 16V				−5.0	
Gate−to−Source Leakage Current	I_{GSS}	P	V_{DS} = 0 V, V_{GS} = ±4.5 V				± 2.0	μA
		N					± 5.0	
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	$V_{GS(TH)}$	N	V_{GS} = V_{DS}	I_D = 250 μA	0.45		1.0	V
		P		I_D = −250 μA	−0.45		−1.0	
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$					−1.9		−mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	N	V_{GS} = 4.5 V, I_D = 540 mA			0.4	0.55	Ω
		P	V_{GS} = −4.5V, I_D = −430 mA			0.5	0.9	
		N	V_{GS} = 2.5 V, I_D = 500 mA			0.5	0.7	
		P	V_{GS} = −2.5V, I_D = −300 mA			0.6	1.2	
		N	V_{GS} = 1.8 V, I_D = 350 mA			0.7	0.9	
		P	V_{GS} = −1.8V, I_D = −150 mA			1.0	2.0	
Forward Transconductance	g_{FS}	N	V_{DS} = 10 V, I_D = 540 mA			1.0		S
		P	V_{DS} = −10 V, I_D = −430 mA			1.0		
CHARGES, CAPACITANCES AND GATE RESISTANCE								
Input Capacitance	C_{ISS}	N	f = 1 MHz, V_{GS} = 0 V V_{DS} = 16 V			80	150	pF
Output Capacitance	C_{OSS}					13	25	
Reverse Transfer Capacitance	C_{RSS}					10	20	
Input Capacitance	C_{ISS}	P	f = 1 MHz, V_{GS} = 0 V V_{DS} = −16 V			105	175	
Output Capacitance	C_{OSS}					15	30	
Reverse Transfer Capacitance	C_{RSS}					10	20	

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Total Gate Charge	$Q_{G(TOT)}$	N	V_{GS} = 4.5 V, V_{DS} = −10 V; I_D = 540 mA		1.5	2.5	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate−to−Source Charge	Q_{GS}				0.2		
Gate−to−Drain Charge	Q_{GD}				0.35		
Total Gate Charge	$Q_{G(TOT)}$	P	V_{GS} = −4.5 V, V_{DS} = 10 V; I_D = −380 mA		1.7	2.5	
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate−to−Source Charge	Q_{GS}				0.3		
Gate−to−Drain Charge	Q_{GD}				0.4		
SWITCHING CHARACTERISTICS (V_{GS} = V) (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	N	V_{GS} = 4.5 V, V_{DD} = −10 V, I_D = 540 mA, R_G = 10 Ω		6.0		ns
Rise Time	t_r				4.0		
Turn−Off Delay Time	$t_{d(OFF)}$				16		
Fall Time	t_f				8.0		
Turn−On Delay Time	$t_{d(ON)}$	P	V_{GS} = −4.5 V, V_{DD} = 10 V, I_D = −215 mA, R_G = 10 Ω		10		
Rise Time	t_r				12		
Turn−Off Delay Time	$t_{d(OFF)}$				35		
Fall Time	t_f				19		
Drain−Source Diode Characteristics							
Forward Diode Voltage	V_{SD}	N	V_{GS} = 0 V, T_J = 25°C · I_S = 350 mA		0.7	1.2	V
		P	I_S = −350 mA		−0.8	−1.2	
Reverse Recovery Time	t_{RR}	N	V_{GS} = 0 V, dIS/dt = 100 A/μs · I_S = 350 mA		6.5		ns
		P	I_S = −350 mA		13		

4. Switching characteristics are independent of operating junction temperatures

N−CHANNEL TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)
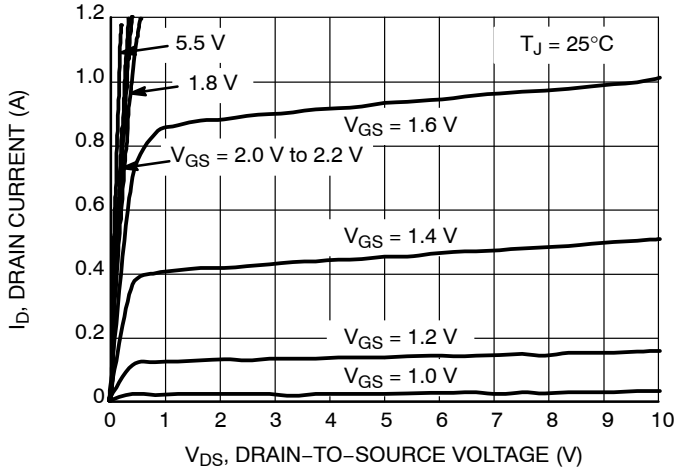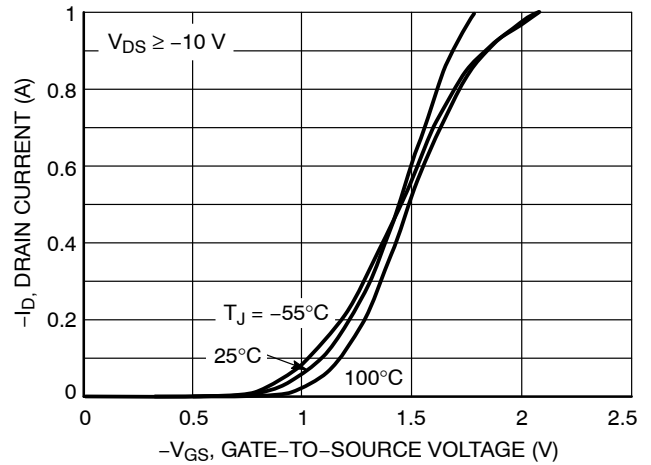
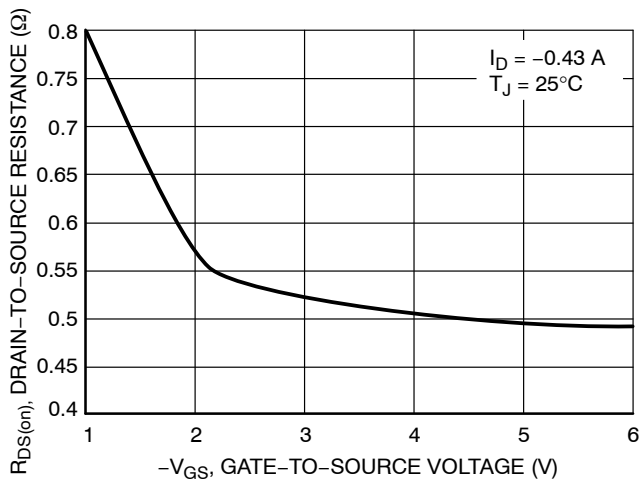**Figure 1. On−Region Characteristics**
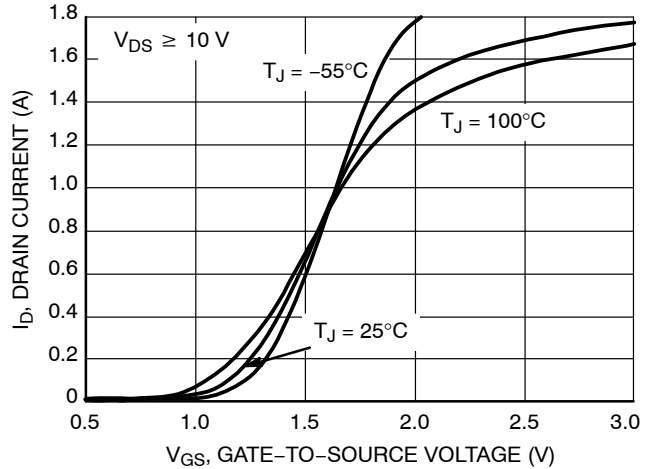
Figure 2. Transfer Characteristics
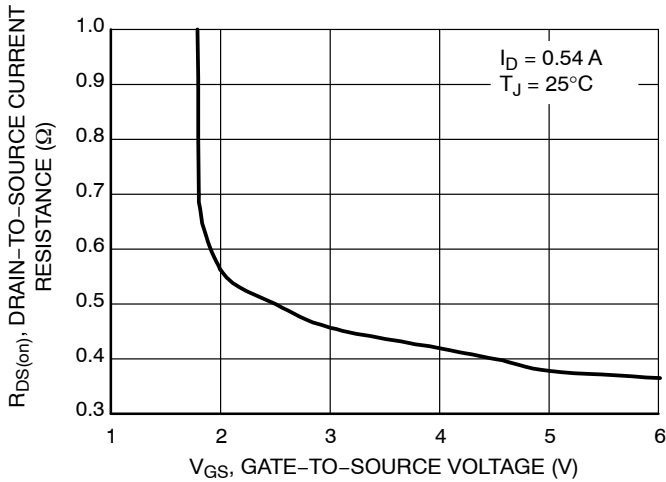
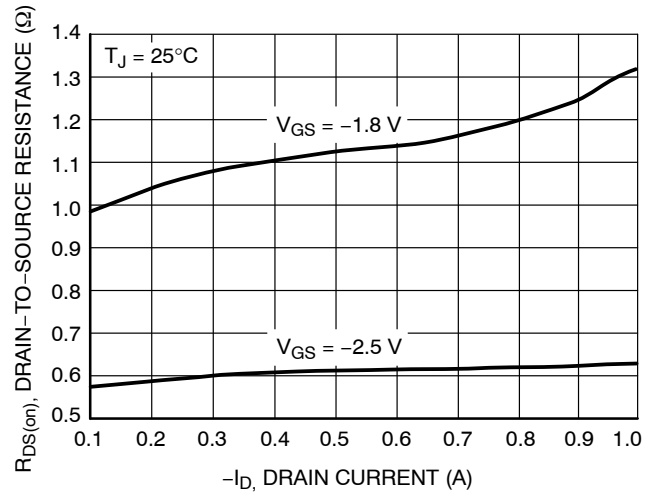**Figure 3. On−Resistance versus
Gate−to−Source Voltage**
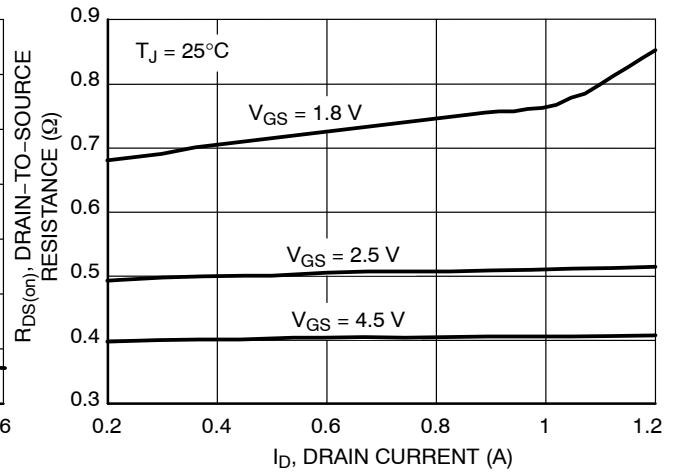
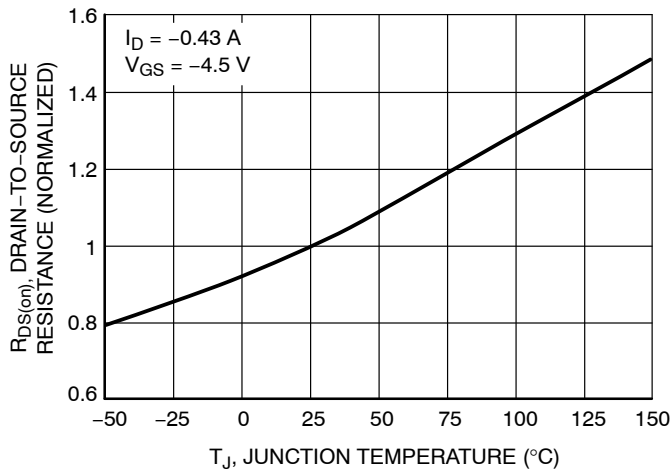**Figure 4. On−Resistance versus Drain Current
and Gate Voltage**
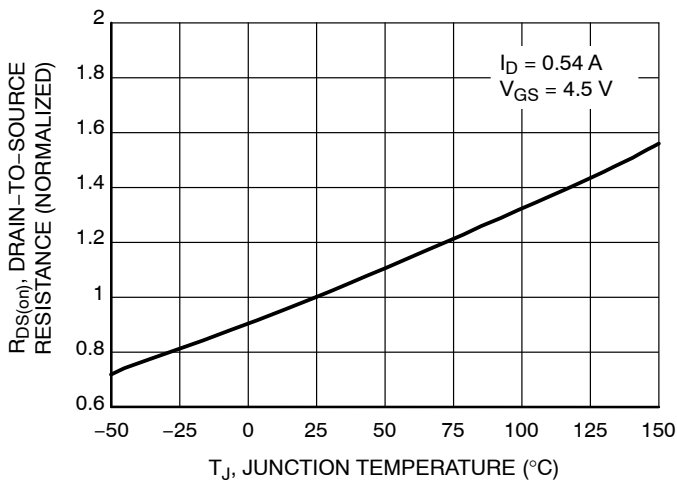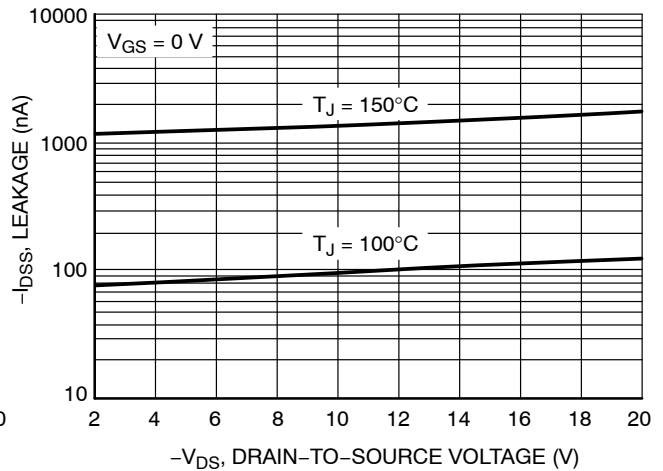
**Figure 5. On−Resistance Variation with
Temperature**
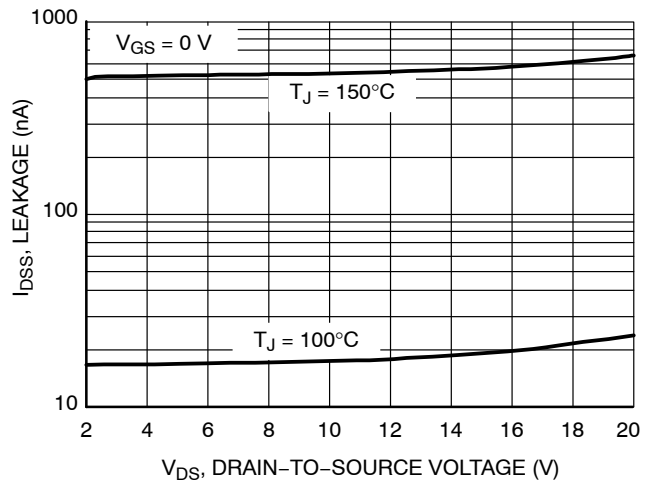
**Figure 6. Drain−to−Source Leakage Current
versus Voltage**

N–CHANNEL TYPICAL PERFORMANCE CURVES $(T_J = 25°C$ unless otherwise noted)
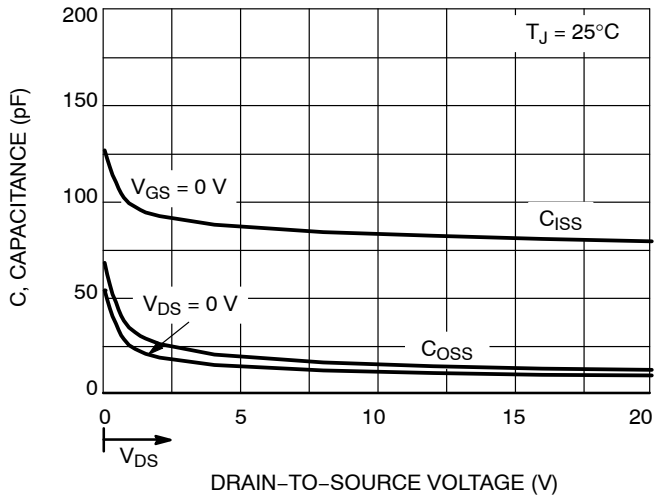
Figure 7. Capacitance Variation
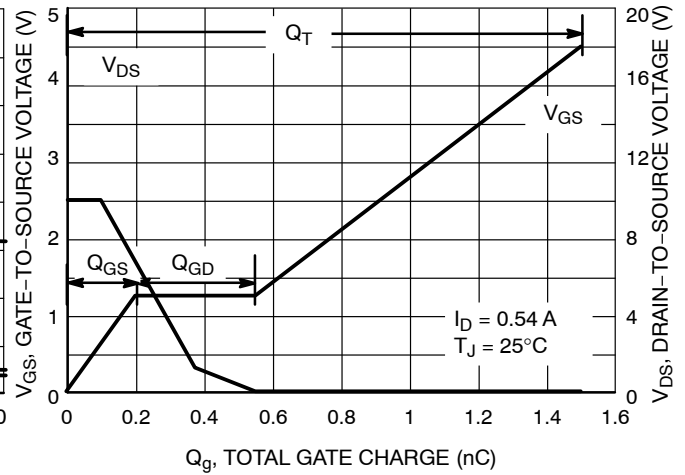
Figure 8. Gate–to–Source and Drain–to–Source Voltage versus Total Charge
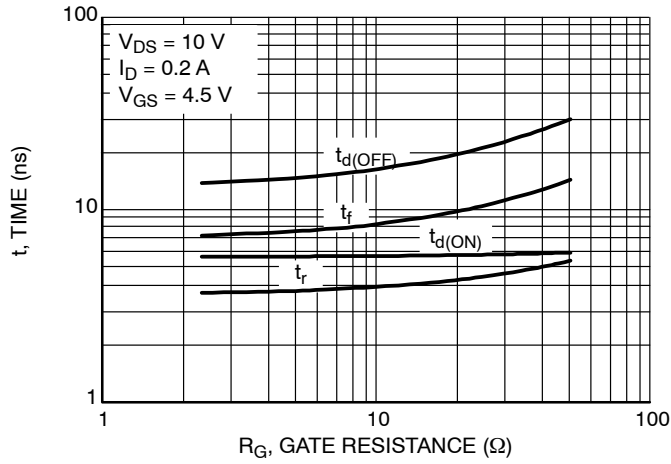
Figure 9. Resistive Switching Time Variation versus Gate Resistance
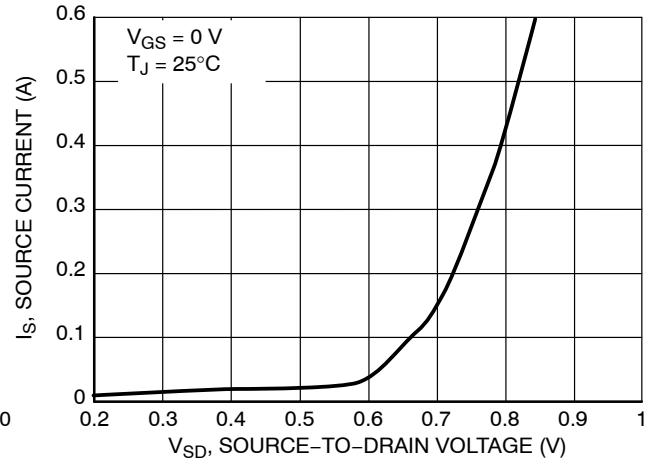
Figure 10. Diode Forward Voltage versus Current

P−CHANNEL TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

Figure 1. On−Region Characteristics

Figure 2. Transfer Characteristics

Figure 3. On−Resistance vs. Gate−to−Source Voltage

Figure 4. On−Resistance vs. Drain Current and Gate Voltage

Figure 5. On−Resistance Variation with Temperature

Figure 6. Drain−to−Source Leakage Current vs. Voltage

NTZD3155C

P–CHANNEL TYPICAL PERFORMANCE CURVES (T$_J$ = 25°C unless otherwise noted)
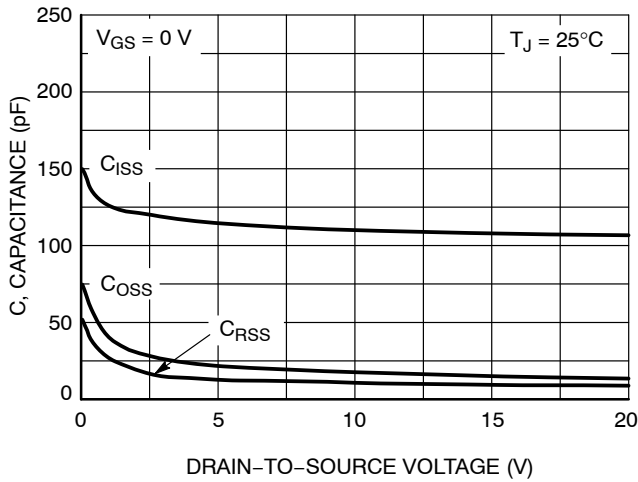
Figure 7. Capacitance Variation
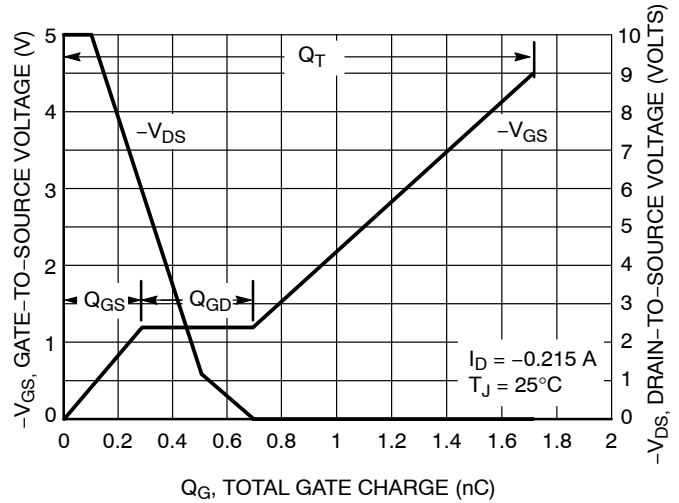
Figure 8. Gate–to–Source and
Drain–to–Source Voltage vs. Total Charge
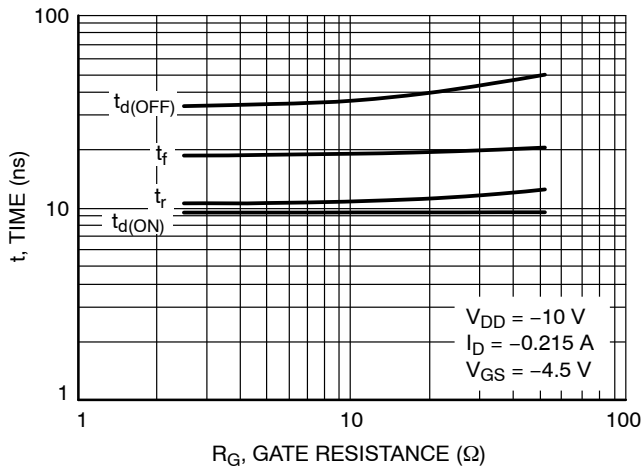
Figure 9. Resistive Switching Time Variation
vs. Gate Resistance
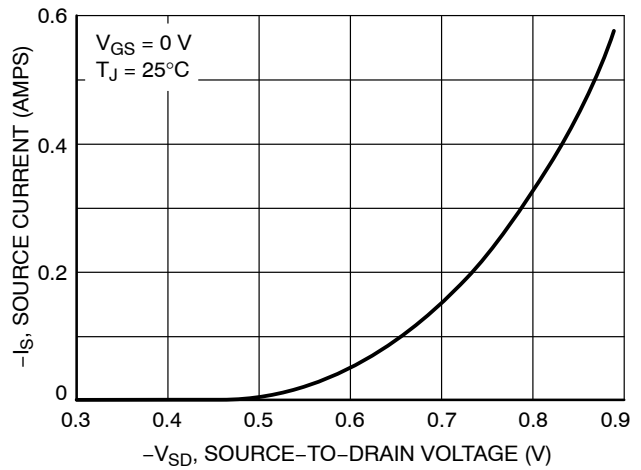
Figure 10. Diode Forward Voltage vs. Current
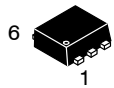
SOT−563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

6

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SCALE 4:1

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

TOP VIEW

SIDE VIEW

RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.
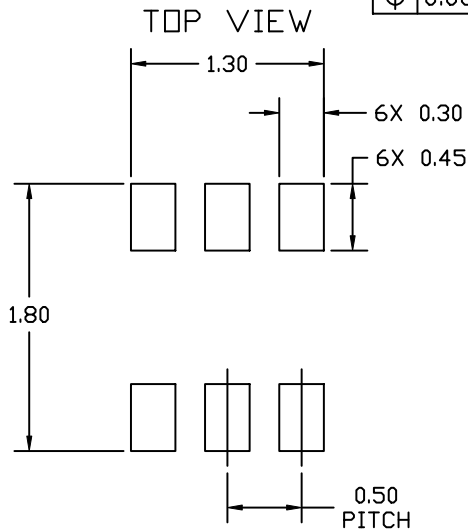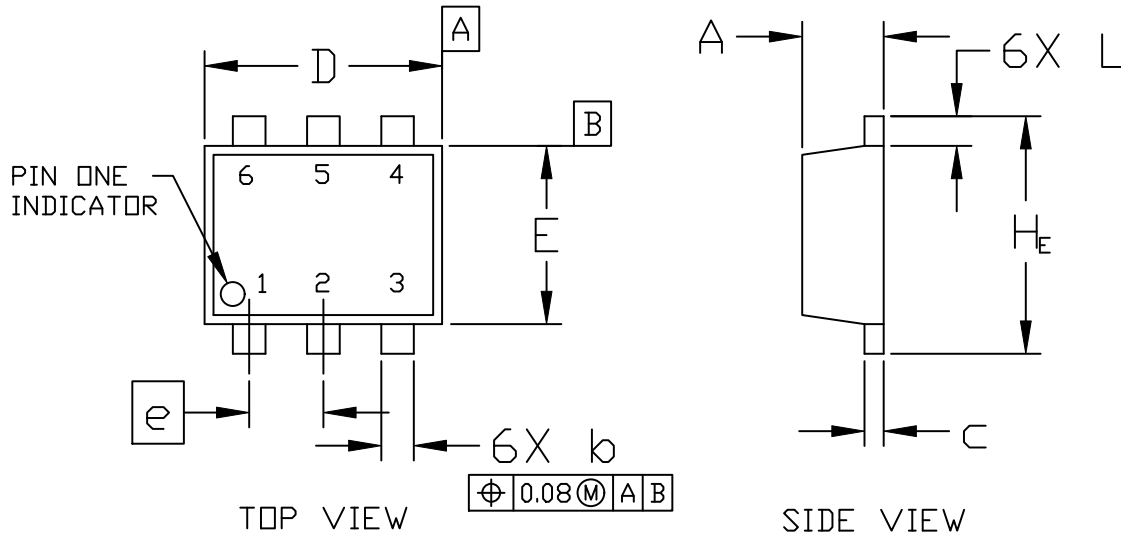
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
L	0.10	0.20	0.30
H_E	1.50	1.60	1.70

DOCUMENT NUMBER:	98AON11126D		
DESCRIPTION:	SOT−563, 6 LEAD		PAGE 1 OF 2

SOT−563, 6 LEAD
CASE 463A
ISSUE H

STYLE 1:
PIN 1. EMITTER 1
    2. BASE 1
    3. COLLECTOR 2
    4. EMITTER 2
    5. BASE 2
    6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
    2. EMITTER 2
    3. BASE 2
    4. COLLECTOR 2
    5. BASE 1
    6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
    2. CATHODE 1
    3. ANODE/ANODE 2
    4. CATHODE 2
    5. CATHODE 2
    6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
    2. COLLECTOR
    3. BASE
    4. EMITTER
    5. COLLECTOR
    6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
    2. CATHODE
    3. ANODE
    4. ANODE
    5. CATHODE
    6. CATHODE

STYLE 6:
PIN 1. CATHODE
    2. ANODE
    3. CATHODE
    4. CATHODE
    5. CATHODE
    6. CATHODE

STYLE 7:
PIN 1. CATHODE
    2. ANODE
    3. CATHODE
    4. CATHODE
    5. ANODE
    6. CATHODE

STYLE 8:
PIN 1. DRAIN
    2. DRAIN
    3. GATE
    4. SOURCE
    5. DRAIN
    6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
    2. GATE 1
    3. DRAIN 2
    4. SOURCE 2
    5. GATE 2
    6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
    2. N/C
    3. CATHODE 2
    4. ANODE 2
    5. N/C
    6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
    2. BASE 2
    3. COLLECTOR 1
    4. EMITTER 1
    5. BASE 1
    6. COLLECTOR 2

GENERIC
MARKING DIAGRAM*
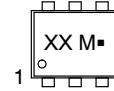
XX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical–documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

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